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1 Electrical ratings

			Value		
Symbol	Parameter	TO-220FP I ² PAKFP	H ² PAK-2	TO-220	Unit
V_{DS}	Drain-source voltage		100		V
V _{GS}	Gate-source voltage		± 20		V
I _D ⁽¹⁾	Drain current (continuous) at $T_{C} = 25^{\circ}C$	46	120		А
I _D ⁽¹⁾	Drain current (continuous) at T _C =100°C	29	7	8	А
I _{DM} ⁽²⁾	Drain current (pulsed)	184	450		А
P _{TOT}	Total dissipation at $T_C = 25^{\circ}C$	35	250		W
dv/dt	Peak diode recovery voltage slope		22		V/ns
V _{ISO}	Insulation withstand voltage (RMS) from all three leads to external heat sink (t = 1 s; $T_C = 25$ °C)	2500			V
E _{AS} ⁽³⁾	Single pulse avalanche energy		125		mJ
T _j T _{stg}	Operating junction temperature storage temperature	-	55 to 175		°C

Table 2.Absolute maximum ratings

1. Current limited by package.

2. Pulse width limited by safe operating area.

3. Starting Tj = 25 °C, I_D = 50 A, V_{DD} = 50 V for TO-220 and H²PAK-2; Starting Tj = 25 °C, I_D = 29 A, V_{DD} = 60 V for I²PAKFP and TO-220FP.

Table 3.Thermal data

			Value		
Symbol	Parameter	TO-220FP I ² PAKFP	H ² PAK-2	TO-220	Unit
Rthj-case	Thermal resistance junction-case	4.3	0.6	0.6	°C/W
Rthj-a	Thermal resistance junction-ambient	62.5		62.5	°C/W
Rthj-pcb ⁽¹⁾	Thermal resistance junction-pcb		35		°C/W

1. When mounted on FR-4 board, on 1inch², 2oz Cu.



2 Electrical characteristics

 $(T_{CASE} = 25 \degree C \text{ unless otherwise specified})$

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
V _{(BR)DSS}	Drain-source breakdown voltage	V _{GS} = 0, I _D = 250 μA	100	-		V
I _{DSS}	Zero gate voltage drain current	$V_{GS} = 0, V_{DS} = 100 V$ $T_{C} = 25^{\circ}C$ $T_{C} = 125^{\circ}C$		-	10 100	μΑ μΑ
I _{GSS}	Gate body leakage current	$V_{DS} = 0, V_{GS} = \pm 20 V$		-	±200	nA
V _{GS(th)}	Gate threshold voltage	V_{DS} = V_{GS} , I_D = 250 μ A	2	-	4	V
B	Static drain-source on-	V _{GS} = 10 V, I _D = 23A TO-220FP and I²PAKFP		8	9.6	mΩ
R _{DS(on)}	resistance	V _{GS} = 10 V, I _D = 60 A H²PAK TO-220		7.8 8	9.3 9.6	11152

Table 4. On/off states

	2 y mainine					
Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
C _{iss} C _{oss} C _{rss}	Input capacitance Output capacitance Reverse transfer capacitance	V _{GS} = 0, V _{DS} = 25 V, f = 1 MHz	-	3305 373 23	-	pF pF pF
Q _g Q _{gs} Q _{gd}	Total gate charge Gate-source charge Gate-drain charge	$V_{DD} = 50 \text{ V}, I_D = 120 \text{ A},$ $V_{GS} = 10 \text{ V}$ (see <i>Figure 20</i>)	-	57 22 17	-	nC nC nC

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
t _{d(on)}	Turn-on delay time	$V_{DD} = 50 \text{ V}, \text{ I}_{D} = 60 \text{ A}$		17		ns
t _r	Rise time	$R_{G} = 4.7 \ \Omega V_{GS} = 10 \ V$	_	38	_	ns
t _{d(off)}	Turn-off delay time	(see Figure 19,	-	52	-	ns
t _f	Fall time	Figure 24)		7.2		ns



Table 7.	Source drain diode					
Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
I _{SD} I _{SDM} ⁽¹⁾	Source-drain current Source-drain current (pulsed)	For TO-220FP and I ² PAKFP	-		46 184	A A
I _{SD} I _{SDM} ⁽²⁾	Source-drain current Source-drain current (pulsed)	For TO-220, H ² PAK-2	-		120 450	A A
		I _{SD} =120 A, V _{GS} =0; for TO-220, H²PAK-2				
V _{SD} ⁽³⁾	Forward on voltage	I _{SD} =46 A, V _{GS} =0; for TO-220FP and I²PAKFP	-		1.5	V
t _{rr} Q _{rr} I _{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	I _{SD} =120 A, di/dt = 100 A/μs, V _{DD} =80 V, Tj=150 °C (see <i>Figure 21</i>)	-	68 182 5.4		ns nC A

Table 7. Source drain diode

1. Pulse width limited by safe operating area

2. Pulse width limited by safe operating area

3. Pulsed: pulse duration = 300 μ s, duty cycle 1.5%



2.1 Electrical characteristics (curves)





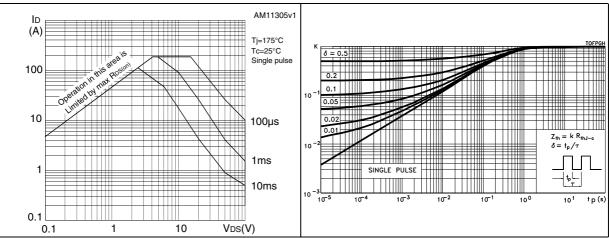
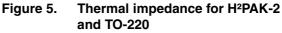
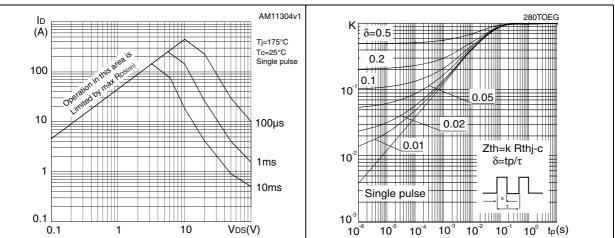


Figure 4. Safe operating area for H²PAK-2 and TO-220









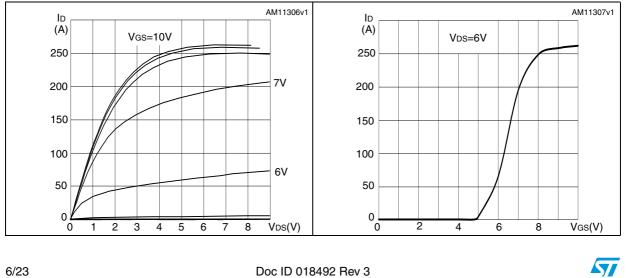


Figure 8. Static drain-source on-resistance for TO-220FP and I²PAKFP

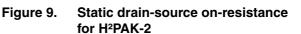


Figure 11. Normalized $B_{VDSS} \ vs$ temperature

Electrical characteristics

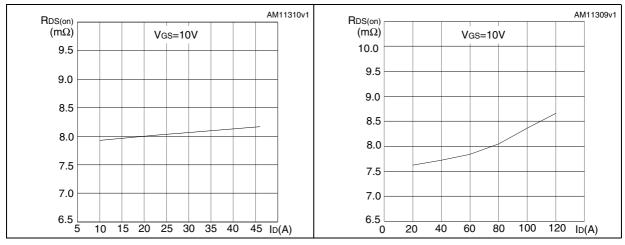
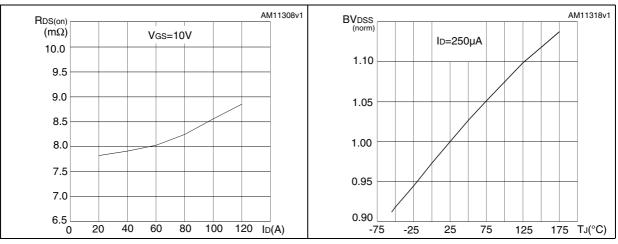
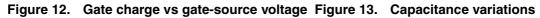


Figure 10. Static drain-source on-resistance for TO-220





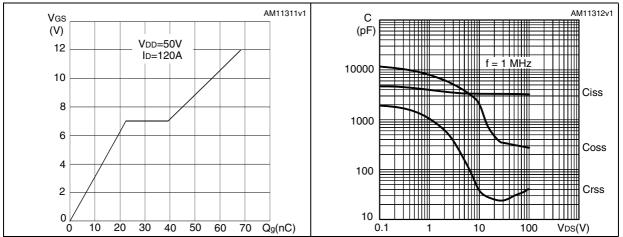
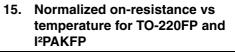


Figure 14. Normalized gate threshold voltage Figure 15. vs temperature



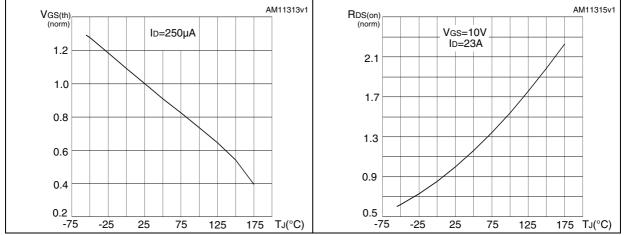
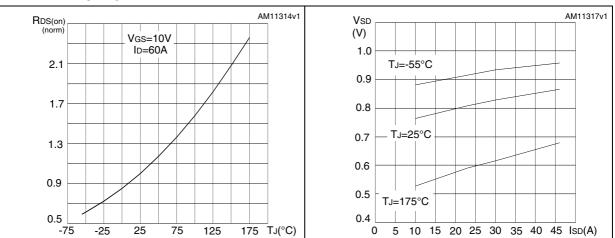


Figure 16. Normalized on resistance vs temperature for H²PAK-2 and TO-220

Figure 17. Source-drain diode forward characteristics for TO-220FP and I²PAKFP





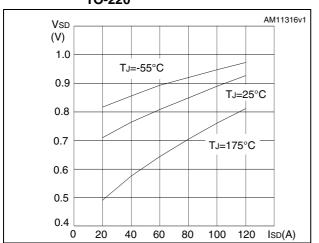


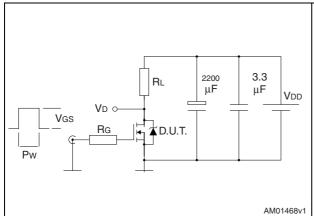
Figure 18. Source-drain diode forward characteristics for H²PAK-2 and TO-220



Figure 20. Gate charge test circuit

3 Test circuits

Figure 19. Switching times test circuit for resistive load



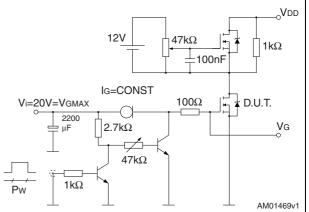
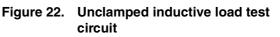
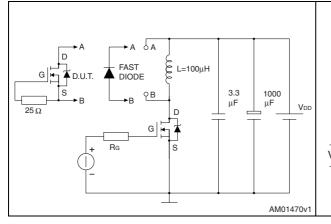


Figure 21. Test circuit for inductive load switching and diode recovery times





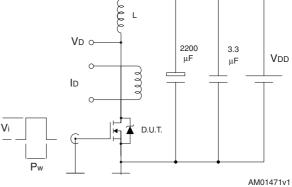
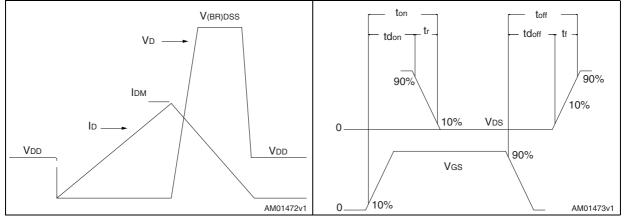




Figure 24. Switching time waveform





4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.



Dim		mm	
Dim.	Min.	Тур.	Max.
A	4.4		4.6
В	2.5		2.7
D	2.5		2.75
E	0.45		0.7
F	0.75		1
F1	1.15		1.70
F2	1.15		1.70
G	4.95		5.2
G1	2.4		2.7
Н	10		10.4
L2		16	
L3	28.6		30.6
L4	9.8		10.6
L5	2.9		3.6
L6	15.9		16.4
L7	9		9.3
Dia	3		3.2

Table 8.TO-220FP mechanical data





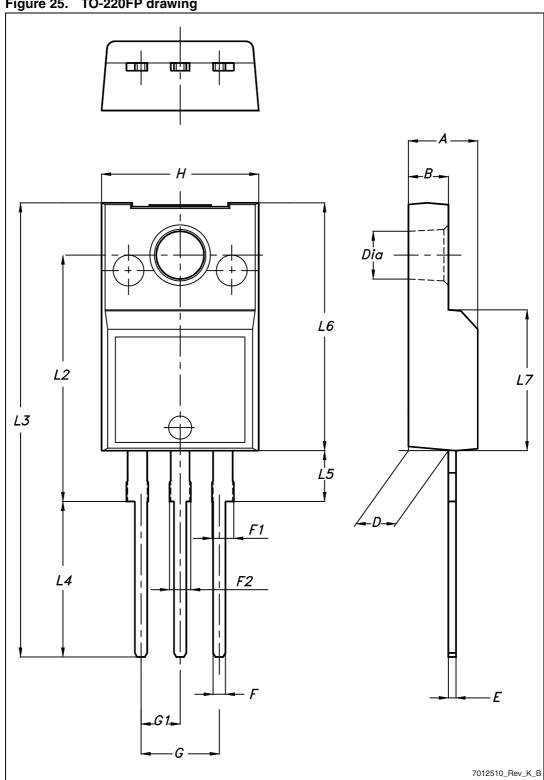


Figure 25. TO-220FP drawing



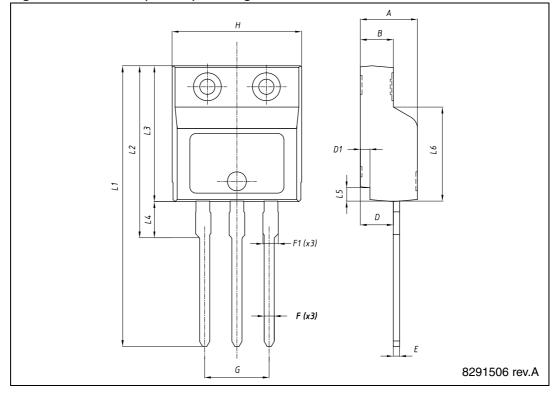
Dim		mm	
Dim.	Min.	Тур.	Max.
A	4.40		4.60
В	2.50		2.70
D	2.50		2.75
D1	0.65		0.85
E	0.45		0.70
F	0.75		1.00
F1			1.20
G	4.95	-	5.20
Н	10.00		10.40
L1	21.00		23.00
L2	13.20		14.10
L3	10.55		10.85
L4	2.70		3.20
L5	0.85		1.25

 Table 9.
 I²PAKFP (TO-281) mechanical data

Figure 26. I²PAKFP (TO-281) drawing

7.30

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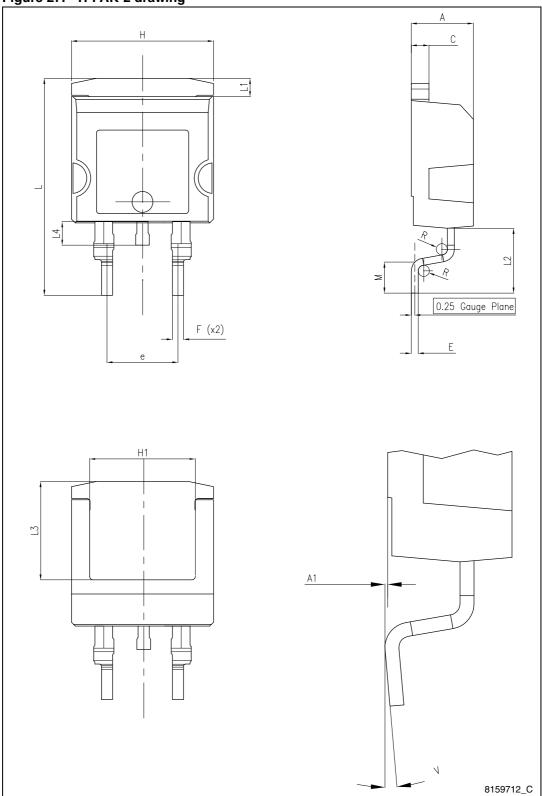
7.50

Dim		mm	
Dim.	Min.	Тур.	Max.
A	4.30		4.80
A1	0.03		0.20
С	1.17		1.37
е	4.98		5.18
E	0.50		0.90
F	0.78		0.85
Н	10.00		10.40
H1	7.40		7.80
L	15.30	-	15.80
L1	1.27		1.40
L2	4.93		5.23
L3	6.85		7.25
L4	1.5		1.7
М	2.6		2.9
R	0.20		0.60
V	0°		8°

Table 10. H²PAK-2 mechanical data



Figure 27. H²PAK-2 drawing





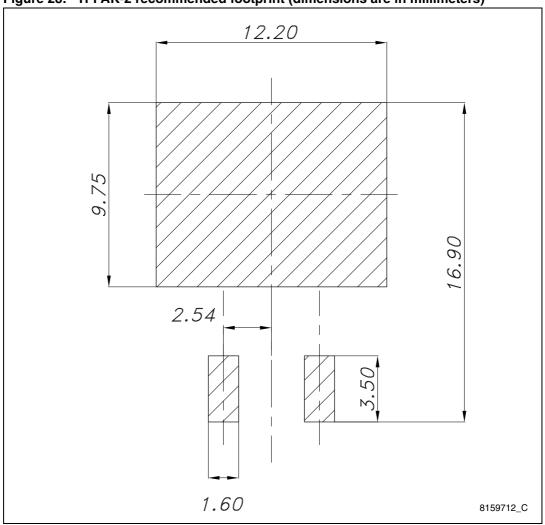


Figure 28. H²PAK-2 recommended footprint (dimensions are in millimeters)



Dim		mm	
Dim.	Min.	Тур.	Max.
А	4.40		4.60
b	0.61		0.88
b1	1.14		1.70
С	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10		10.40
е	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13		14
L1	3.50		3.93
L20		16.40	
L30		28.90	
ØР	3.75		3.85
Q	2.65		2.95

Table 11. TO-220 type A mechanical data



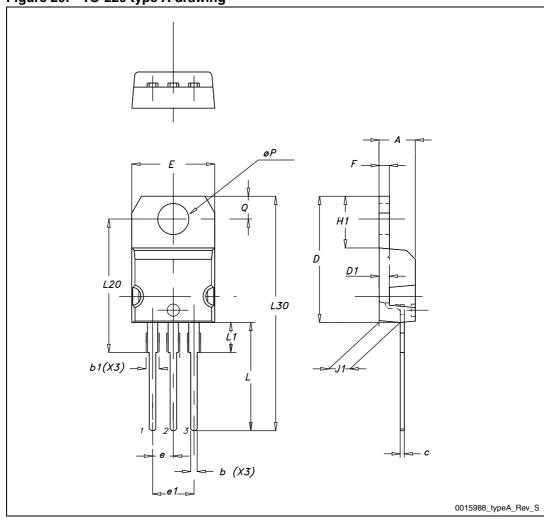


Figure 29. TO-220 type A drawing



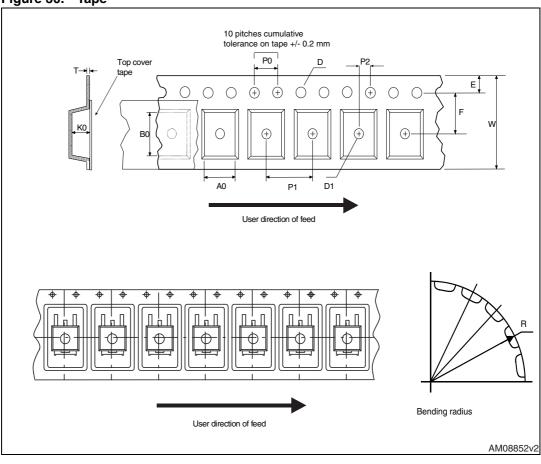
5 Package mechanical data

Таре			Reel			
Dim	mm		Dim	mm		
Dim. —	Min.	Max.	— Dim. –	Min.	Max.	
A0	10.5	10.7	А		330	
B0	15.7	15.9	В	1.5		
D	1.5	1.6	С	12.8	13.2	
D1	1.59	1.61	D	20.2		
Е	1.65	1.85	G	24.4	26.4	
F	11.4	11.6	Ν	100		
K0	4.8	5.0	Т		30.4	
P0	3.9	4.1				
P1	11.9	12.1		Base qty 1000		
P2	1.9	2.1		Bulk qty 1000		
R	50					
Т	0.25	0.35				
W	23.7	24.3				

Table 12. H²PAK-2 tape and reel mechanical data

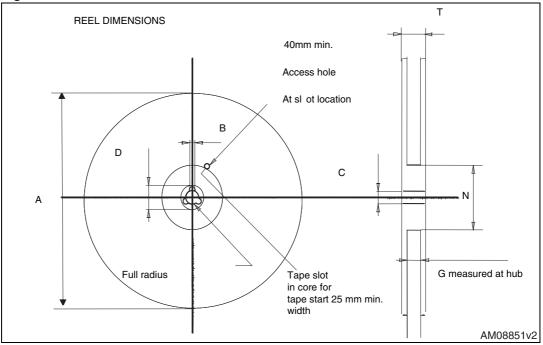
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6 Revision history

Table 13.	Document revision history
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Date	Revision	Changes
24-Feb-2011	1	First version.
07-May-2012	2	Added <i>Section 2.1: Electrical characteristics (curves).</i> Minor text changes.
07-Nov-2012	3	Added new device in I ² PAKFP and updated the document accordingly. Updated <i>Section 4: Package mechanical data</i> .

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